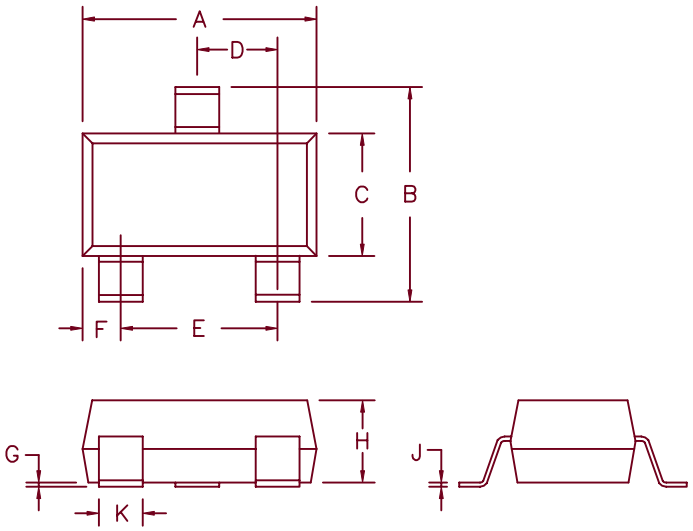
200 mW Schottky Diode
BAT54, BAT54A, BAT54C, BAT54S



Dim.	Inches		Millimeter		
	Minimum	Maximum	Minimum	Maximum	Notes
A	.110	.120	2.80	3.04	
B	.083	.098	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	0.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	0.45	0.06	
G	.0005	.0039	0.013	0.100	
H	.035	.044	0.89	1.12	
J	.003	.007	0.085	0.18	
K	.015	.020	0.37	0.51	

SOT–23

Microsemi Catalog Number	Peak Reverse Voltage	Pin Configuration	Type
BAT54	30V	Figure 1	Single
BAT54A	30V	Figure 2	Dual
BAT54C	30V	Figure 3	Dual
BAT54S	30V	Figure 4	Dual

Pin Configuration – Top View

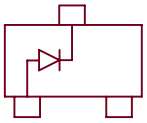


Figure 1 54

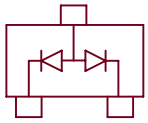


Figure 2 54A

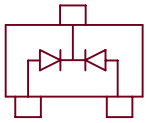


Figure 3 54C

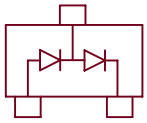


Figure 4 54S

Electrical Characteristics

Total Power Dissipation	P_D 200 mW	T_A = 25°C
Maximum forward voltage drop	V_{FM} 0.32 Volts	I_{FM} = 1mA, T_J = 25°C*
	V_{FM} 0.50 Volts	I_{FM} = 30mA: T_J = 25°C*
Maximum reverse current	I_R 2.0 µA	V_R = 25V, T_J = 25°C
Non–repetitive peak forward current	I_{FSM} 600 mA	Pulse ≤ 1 second
Typical junction capacitance	C_J 10 pF	1.0 MHz, V_R = 1.0V, 25°C
Reverse recovery time	t_{rr} 5 nS	I_F = I_R = 10 mA, $I_{(REC)}$ = 1 mA

*Pulse test: Pulse width 300 µsec, Duty cycle 2%

Thermal and Thermal Characteristics

Storage temperature range	T_{STG}	–55°C to 150°C
Operating junction temp range	T_J	–55°C to 125°C
Maximum thermal resistance	$R_{\theta JA}$	160°C/W Junction to ambient

3–25–02 Rev. 1

COLORADO Microsemi
800 Hoyt Street
Broomfield, CO. 80020
PH: (303) 469–2161
FAX: (303) 466–3775
www.microsemi.com